

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ C7

650V CoolMOS™ C7 Power Transistor
IPB65R125C7

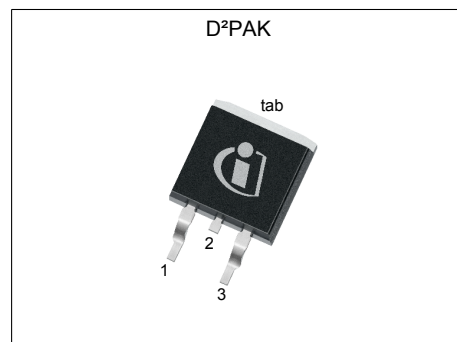
Data Sheet

Rev. 2.0
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

CoolMOS™ C7 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The product portfolio provides all benefits of fast switching superjunction MOSFETs offering better efficiency, reduced gate charge, easy implementation and outstanding reliability.



Features

- Increased MOSFET dv/dt ruggedness
- Better efficiency due to best in class FOM $R_{DS(on)} \cdot E_{oss}$ and $R_{DS(on)} \cdot Q_g$
- Best in class $R_{DS(on)}$ /package
- Easy to use/drive
- Pb-free plating, halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Benefits

- Enabling higher system efficiency
- Enabling higher frequency / increased power density solutions
- System cost / size savings due to reduced cooling requirements
- Higher system reliability due to lower operating temperatures

Applications

PFC stages and hard switching PWM stages for e.g. Computing, Server, Telecom, UPS and Solar.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

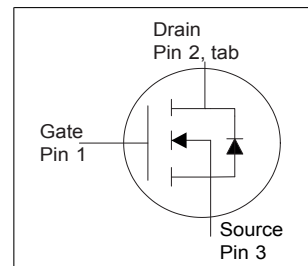


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	125	mΩ
$Q_{g,typ}$	35	nC
$I_{D,pulse}$	75	A
$E_{oss}@400V$	4.2	μJ
Body diode di/dt	55	A/μs

Type / Ordering Code	Package	Marking	Related Links
IPB65R125C7	PG-TO 263	65C7125	see Appendix A

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	18 12	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	75	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	89	mJ	$I_D=7.1\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	0.44	mJ	$I_D=7.1\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, single pulse	I_{AS}	-	-	7.1	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	101	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	n.a.	Ncm	-
Continuous diode forward current	I_S	-	-	18	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	75	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	1	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	55	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$.

²⁾ Pulse width t_p limited by $T_{j,max}$.

³⁾ Identical low side and high side switch with identical R_G .

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.24	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	45	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wave- & reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0V$, $I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$, $I_D=0.44mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650$, $V_{GS}=0V$, $T_j=25^\circ\text{C}$ $V_{DS}=650$, $V_{GS}=0V$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V$, $V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.111 0.265	0.125 -	Ω	$V_{GS}=10V$, $I_D=8.9A$, $T_j=25^\circ\text{C}$ $V_{GS}=10V$, $I_D=8.9A$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	1	-	Ω	$f=1MHz$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	1670	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Output capacitance	C_{oss}	-	26	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	53	-	pF	$V_{GS}=0V$, $V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	579	-	pF	$I_D=\text{constant}$, $V_{GS}=0V$, $V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	14	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=8.9A$, $R_G=10\Omega$; see table 9
Rise time	t_r	-	15	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=8.9A$, $R_G=10\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	71	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=8.9A$, $R_G=10\Omega$; see table 9
Fall time	t_f	-	8	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=8.9A$, $R_G=10\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	8	-	nC	$V_{DD}=400V$, $I_D=8.9A$, $V_{GS}=0$ to $10V$
Gate to drain charge	Q_{gd}	-	11	-	nC	$V_{DD}=400V$, $I_D=8.9A$, $V_{GS}=0$ to $10V$
Gate charge total	Q_g	-	35	-	nC	$V_{DD}=400V$, $I_D=8.9A$, $V_{GS}=0$ to $10V$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=400V$, $I_D=8.9A$, $V_{GS}=0$ to $10V$

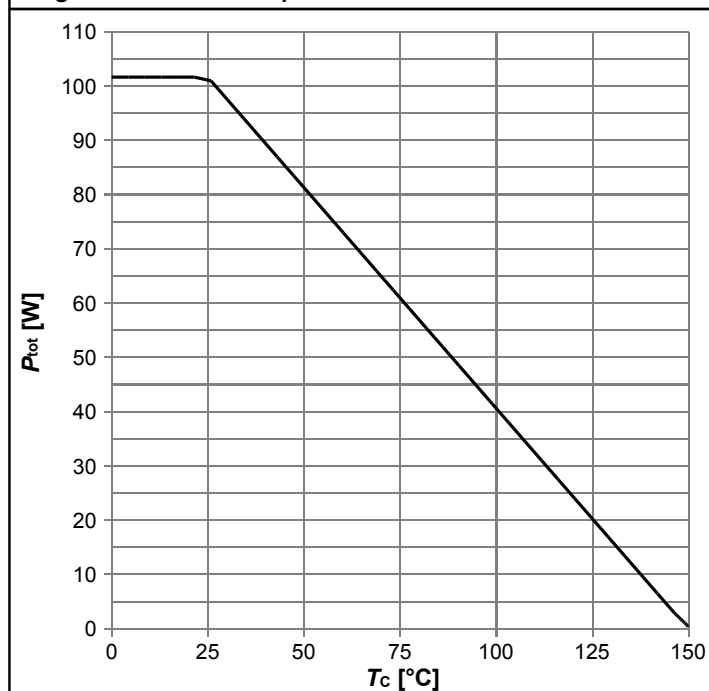
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

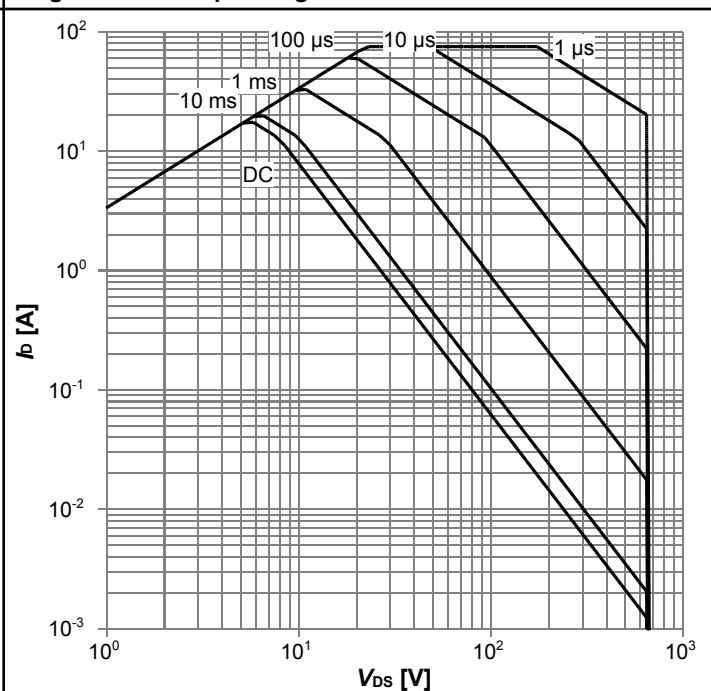
Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=8.9A$, $T_j=25^{\circ}C$
Reverse recovery time	t_{rr}	-	800	-	ns	$V_R=400V$, $I_F=18A$, $di_F/dt=55A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	7	-	μC	$V_R=400V$, $I_F=18A$, $di_F/dt=55A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	20	-	A	$V_R=400V$, $I_F=18A$, $di_F/dt=55A/\mu s$; see table 8

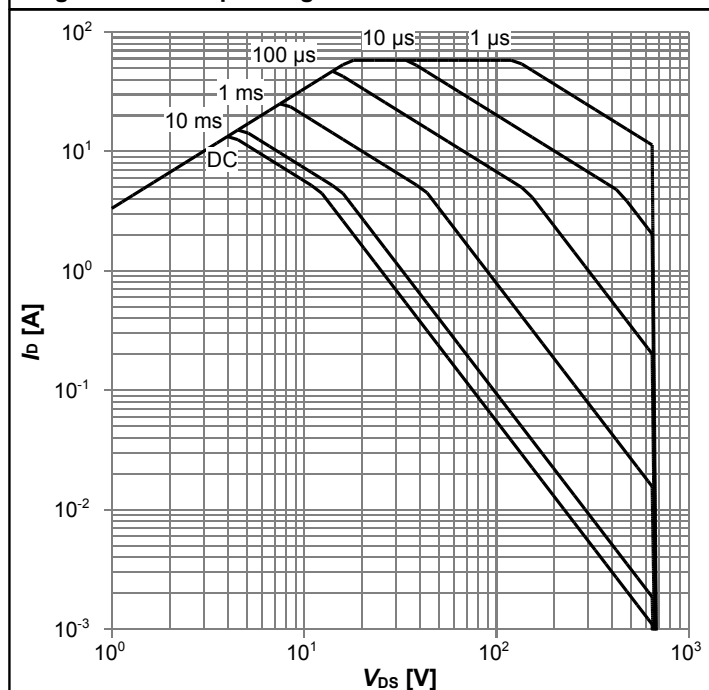
5 Electrical characteristics diagrams

Diagram 1: Power dissipation


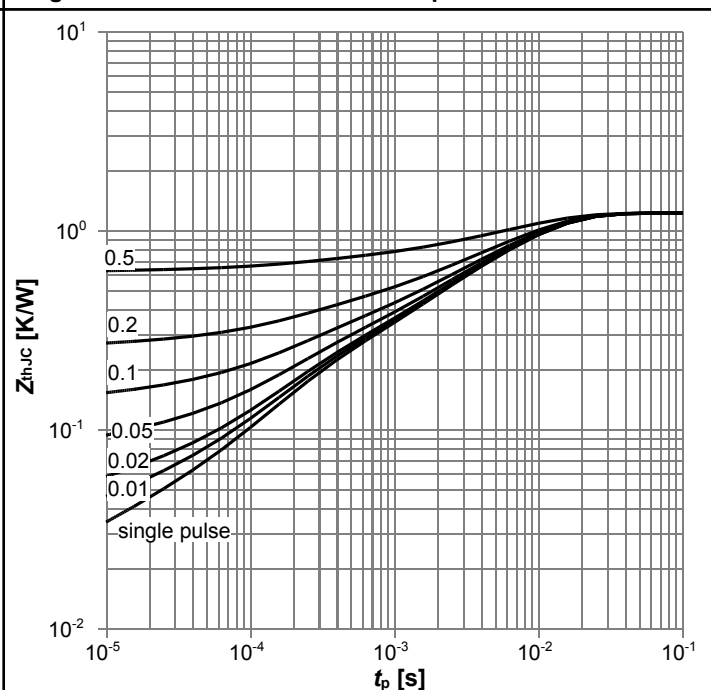
$$P_{tot}=f(T_c)$$

Diagram 2: Safe operating area


$$I_D=f(V_{DS}); T_c=25\text{ °C}; D=0; \text{parameter: } t_p$$

Diagram 3: Safe operating area


$$I_D=f(V_{DS}); T_c=80\text{ °C}; D=0; \text{parameter: } t_p$$

Diagram 4: Max. transient thermal impedance


$$Z_{thJC}=f(t_p); \text{parameter: } D=t_p/T$$

Diagram 5: Typ. output characteristics

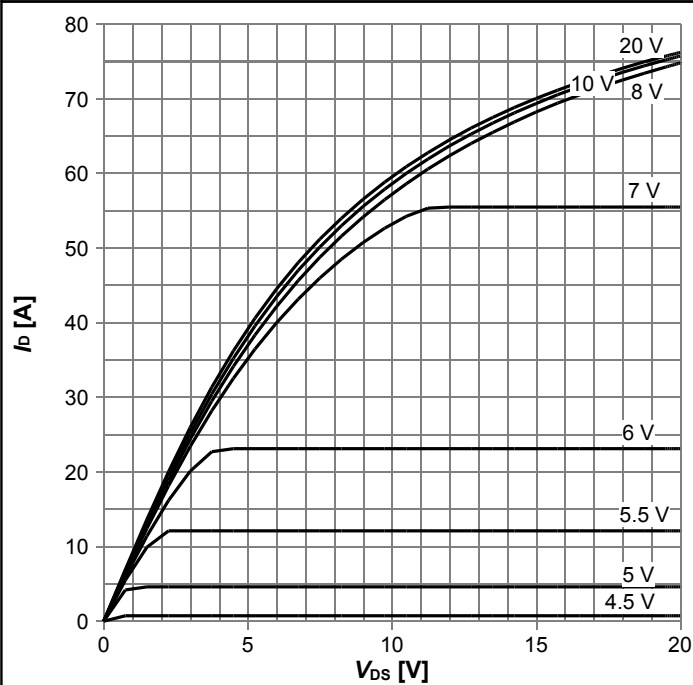

 $I_D = f(V_{DS}); T_J = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. output characteristics

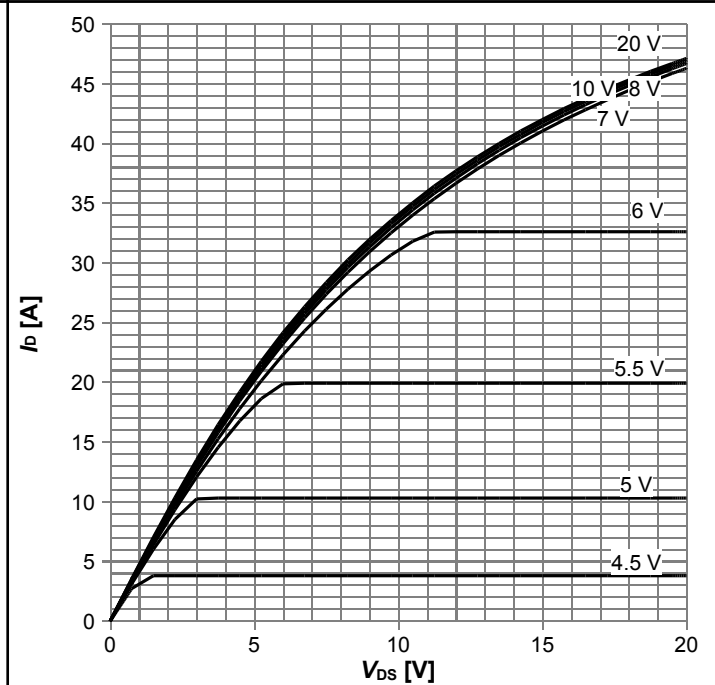

 $I_D = f(V_{DS}); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. drain-source on-state resistance

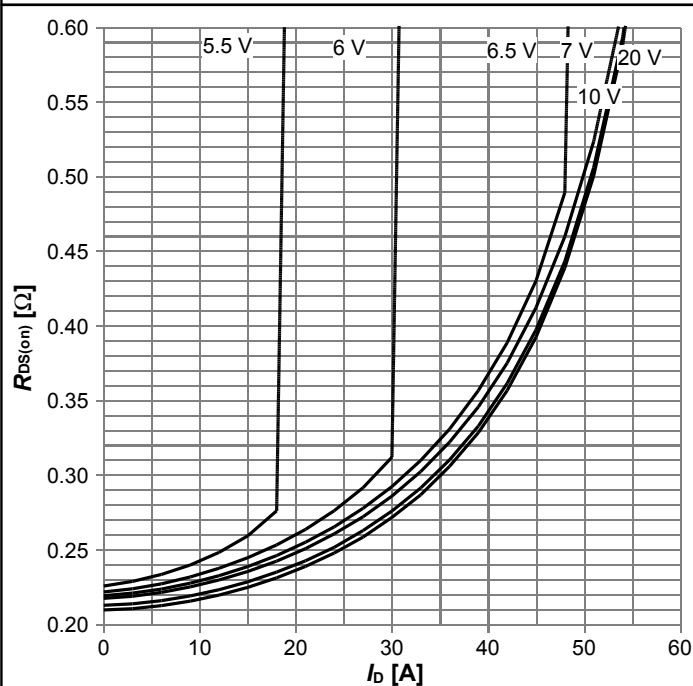

 $R_{DS(on)} = f(I_D); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 8: Drain-source on-state resistance

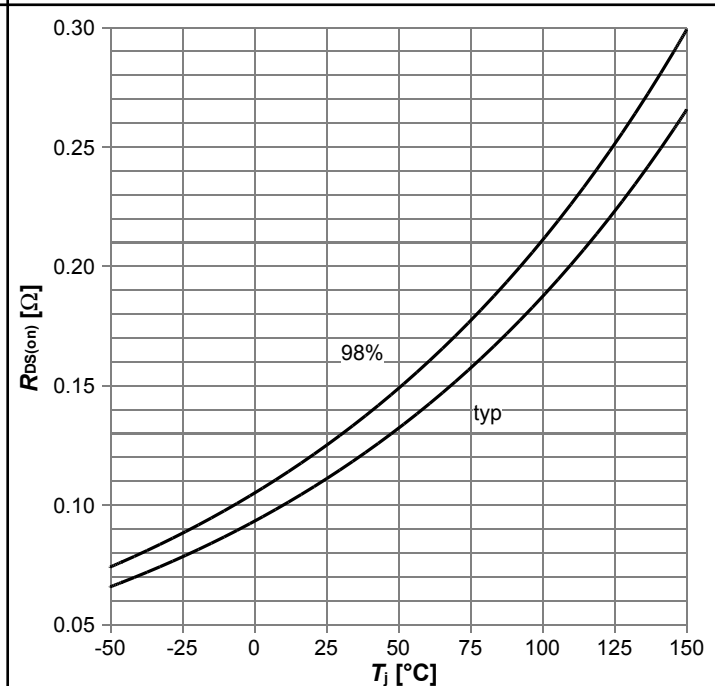

 $R_{DS(on)} = f(T_J); I_D = 8.9\text{ A}; V_{GS} = 10\text{ V}$

Diagram 9: Typ. transfer characteristics

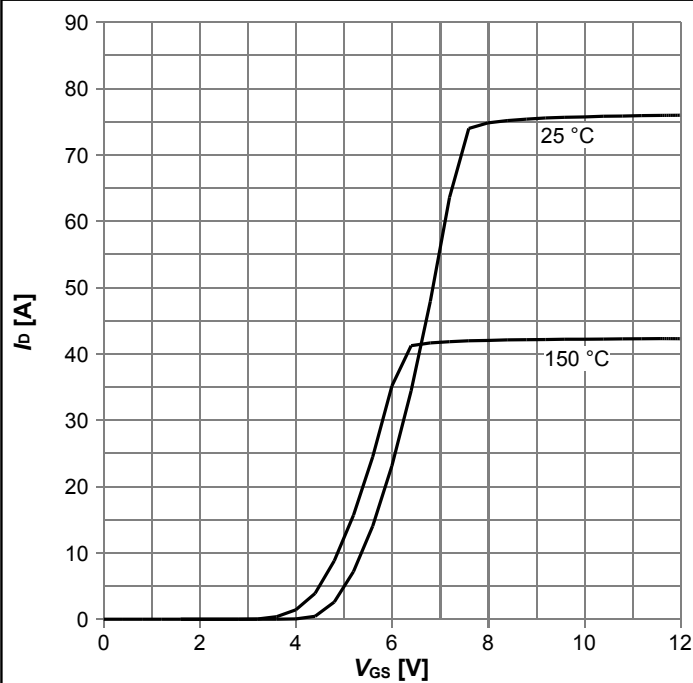

 $I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge

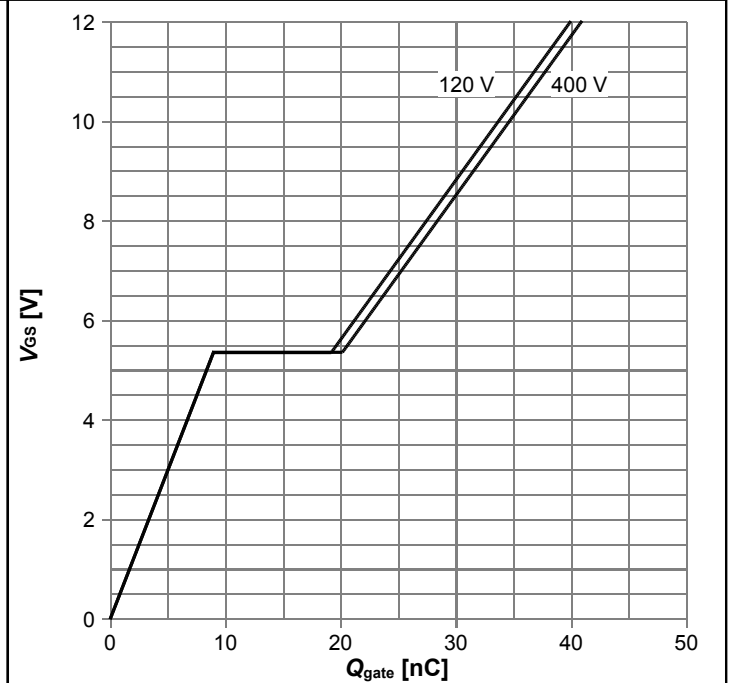

 $V_{GS} = f(Q_{gate}); I_D = 8.9A \text{ pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode

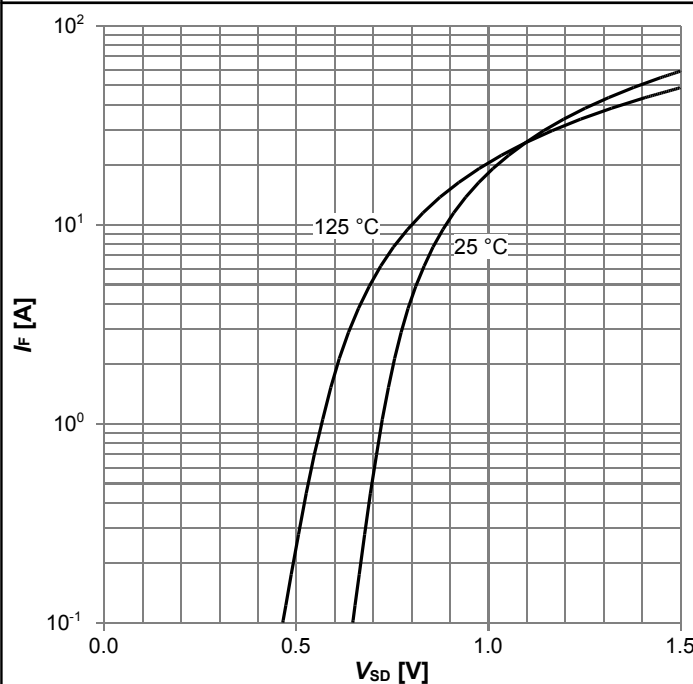

 $I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 12: Avalanche energy

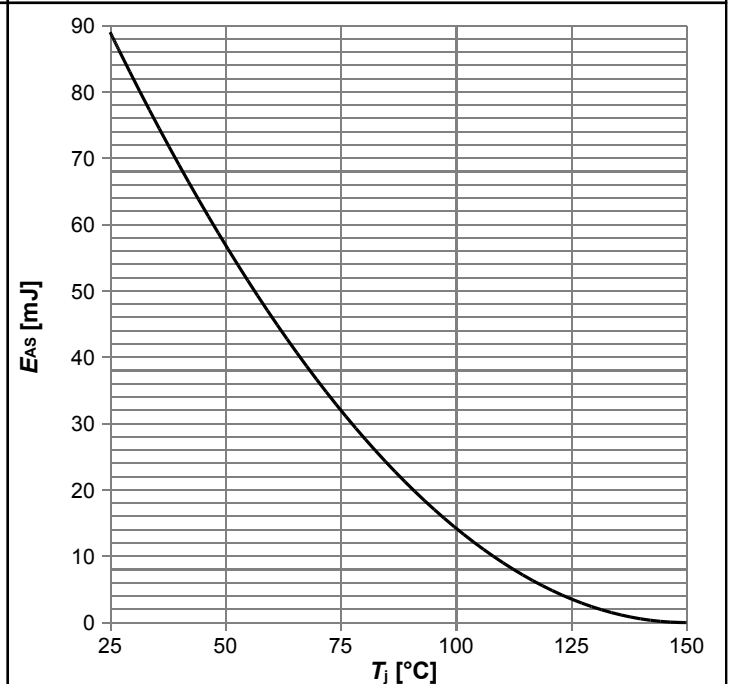
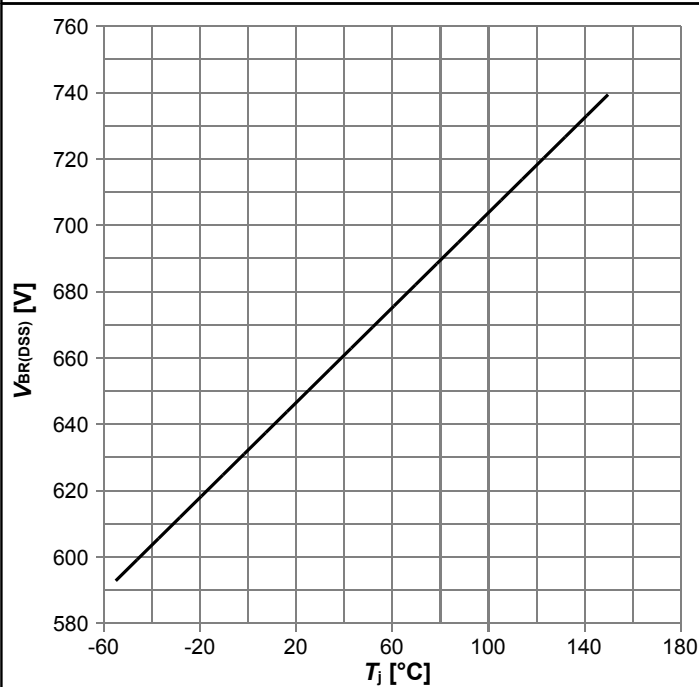
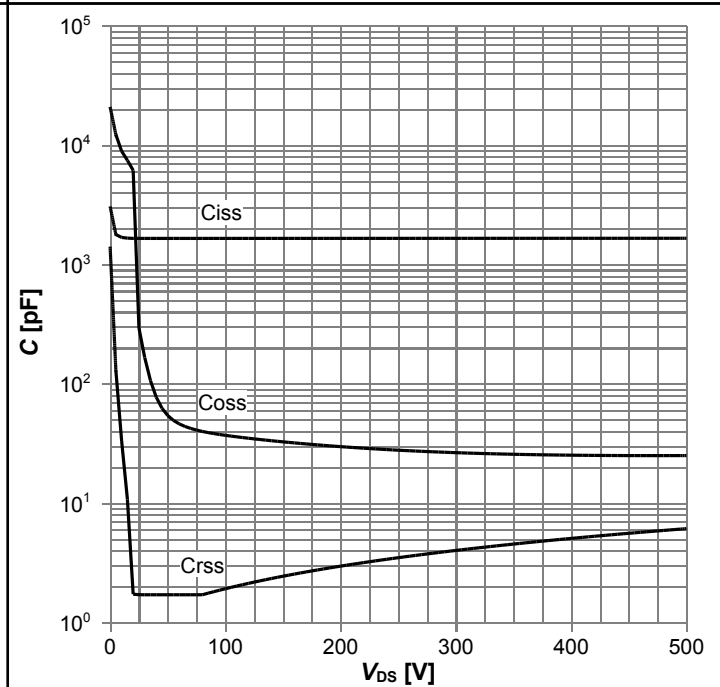

 $E_{AS} = f(T_j); I_D = 7.1 A; V_{DD} = 50 V$

Diagram 13: Drain-source breakdown voltage



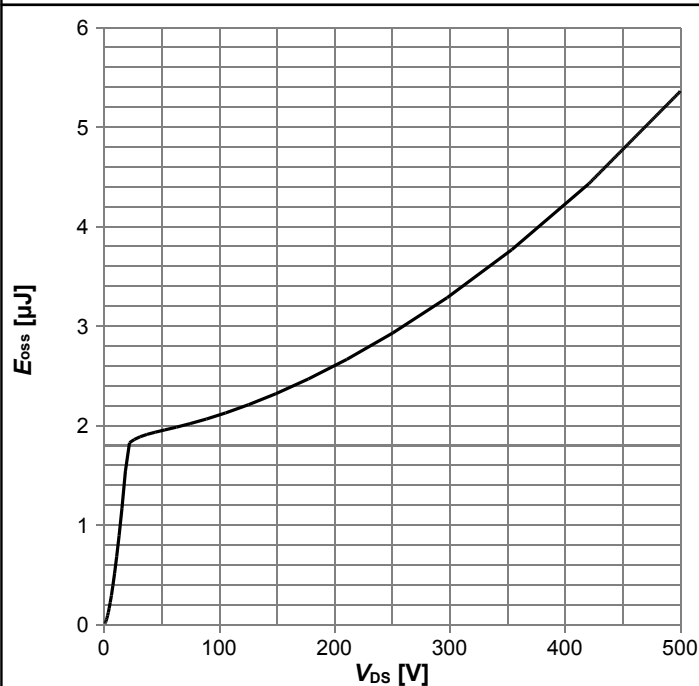
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 14: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$$

Diagram 15: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

6 Test Circuits

Table 8 Diode characteristics

Test circuit for diode characteristics

The test circuit consists of two diodes connected in series. The first diode is driven by a voltage source V_{DS} through a resistor R_{g1} . The second diode is driven by a current source I_F through a resistor R_{g2} . The load resistor R_L is connected in series with the second diode. The condition $R_{g1} = R_{g2}$ is specified.

Diode recovery waveform

The waveform shows the diode's behavior during switching. The forward current I_F is applied for a duration t_F , during which the forward charge Q_F is stored. When the current is reversed to I_{rm} , the reverse recovery time t_{rr} is the time from the start of reverse current to the point where the current reaches $10\% I_{rm}$. The storage time t_S is the time from the end of forward current to the start of reverse current. The total reverse recovery time is $t_{rr} = t_F + t_S$. The reverse charge Q_S is the area under the reverse current curve during t_S . The total reverse charge is $Q_{rr} = Q_F + Q_S$.

Table 9 Switching times

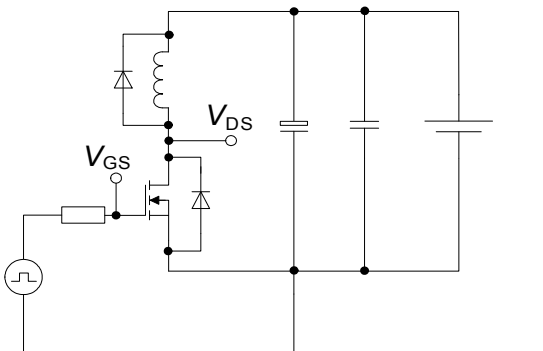
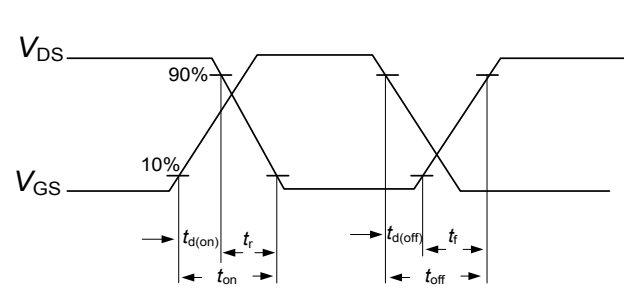
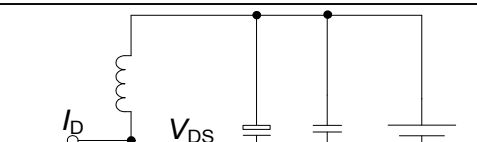
Switching times test circuit for inductive load	Switching times waveform
 The diagram illustrates a switching circuit for an inductive load. A MOSFET is driven by a pulse generator connected to its gate through a resistor. The drain of the MOSFET is connected to an inductive load (represented by an inductor and a diode in parallel) and a DC voltage source. The gate-source voltage is labeled V_{GS} and the drain-source voltage is labeled V_{DS}.	 The diagram shows the switching waveforms for V_{DS} and V_{GS}. The gate voltage V_{GS} transitions from a low level to a high level (turn-on) and back to low (turn-off). The drain voltage V_{DS} transitions from a high level to a low level (turn-on) and back to high (turn-off). The switching times are defined as follows: $t_{d(on)}$: Delay time from the start of V_{GS} rise to 10% of V_{GS} to the start of V_{DS} fall. t_r: Rise time of V_{GS} from 10% to 90%. t_{on}: Total turn-on time from the start of V_{GS} rise to the start of V_{DS} fall. $t_{d(off)}$: Delay time from the start of V_{GS} fall to 90% of V_{GS} to the start of V_{DS} rise. t_f: Fall time of V_{GS} from 90% to 10%. t_{off}: Total turn-off time from the start of V_{GS} fall to the start of V_{DS} rise.

Table 10 **Unclamped inductive load**

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines

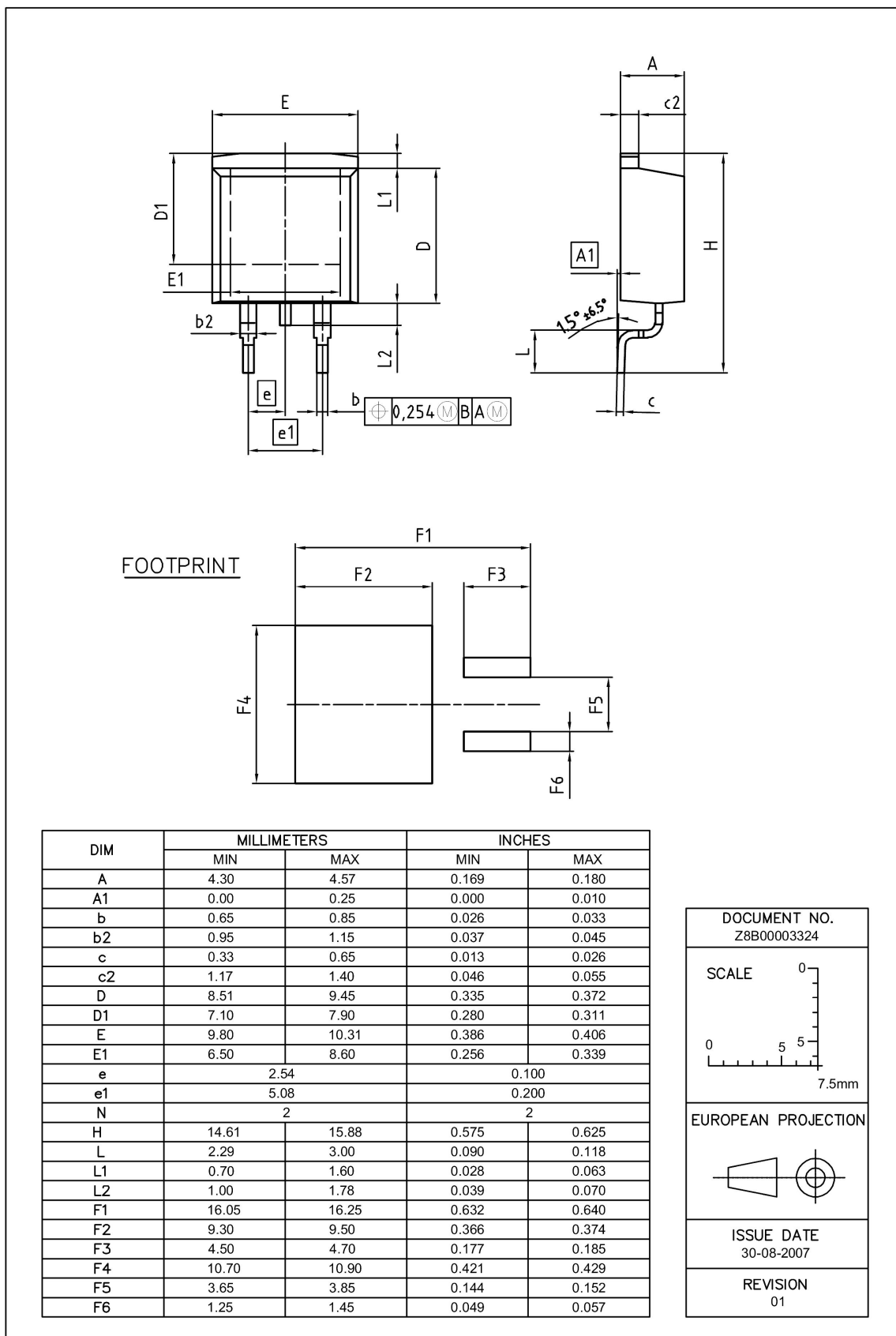


Figure 1 Outline PG-TO 263, dimensions in mm/inches

8 Appendix A

Table 11 Related Links

- IFX CoolMOS™ C7 Webpage: www.infineon.com
- IFX CoolMOS™ C7 application note: www.infineon.com
- IFX CoolMOS™ C7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPB65R125C7

Revision: 2013-10-11, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2013-10-11	Release of final version

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

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The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.